

ABSTRACT

Sensing circuitry for reading and verifying the contents of electrically programmable and erasable non-volatile memory cells, comprises a sense amplifier having a first sensing circuit portion connected to a cell to be read and provided with an output terminal for connection to a first input terminal of a comparator, and having a second reference circuit portion connected to a reference current generator and provided with an output terminal for connection to a second input terminal of said comparator, characterized in that said first and said second circuit portions comprise a series of first and second transistors, respectively, being connected between a first voltage reference and a second voltage reference and having respective points of interconnection connected to said output terminals of said first and second circuit portions.